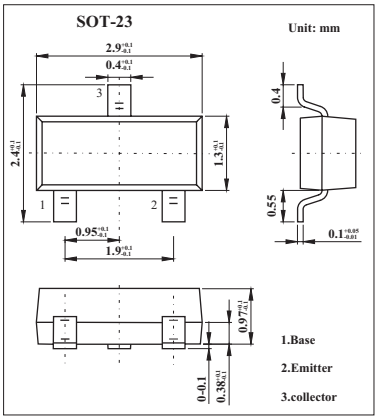
PNP Epitaxial Planar Silicon Transistors

2SB1295



■ Features

- Large current capacity.
- Low collector to emitter saturation voltage.
- Very small-sized package permitting sets to be made smaller and slimer.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-15	V
Collector-emitter voltage	V_{CEO}	-15	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-0.8	A
Collector current (pulse)	I_{CP}	-3	A
Collector dissipation	P_C	200	mW
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = -12V , I_E = 0			-100	nA
Emitter cutoff current	I_{EBO}	V_{EB} = -4V , I_C = 0			-100	nA
DC current Gain	h_{FE}	V_{CE} = -2V , I_C = -50mA	135		600	
Gain bandwidth product	f_T	V_{CE} = -2V , I_C = -50mA		300		MHz
Output capacitance	C_{ob}	V_{CB} = -10V , f = 1MHz		15		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -5mA , I_B = -0.5mA		-10	-25	mV
	$V_{CE(sat)}$	I_C = -400mA , I_B = -20mA		-100	-200	mV
Base-to-emitter saturation voltage	$V_{BE(sat)}$	I_C = -400mA , I_B =-20mA		-0.9	-1.2	V
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	I_C = -10μA , I_E = 0	-15			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -1mA , R_{BE} = ∞	-15			V
Emitter-to-base breakdown voltage	$V_{(BR)EBO}$	I_E = -10μA , I_C = 0	-5			V

■ h_{FE} Classification

Marking	UL		
Rank	5	6	7
hFE	135～270	200～400	300～600